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INFORMATION DISCLOSURE STATEMENT		Applicant: Hisashi OHTANI et al.	
(Use several sheets if necessary)		Filing Date: February 27, 1997	Group: 2813

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EP		Y. Kawazu et al, Jpn. J. Appl Phys, 29, 12 (1990) pp. 2698-2704 "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"
EP		T. Sato et al., Physical Review B, Vo. 4, No. 6, 1971, pp.1950-1960 "Mobility Anisotropy of Electrons in Inversion Layers on Oxidized Silicon Surfaces"

Examiner:

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